Switch Mode Power Rectifier

MBR3045WTG

These state-of-the-art devices use the Schottky Barrier principle with a platinum barrier metal.

Features

- Dual Diode Construction; Terminals 1 and 3 may be Connected for Parallel Operation at Full Rating
- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Popular TO-247 Package
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 4.3 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	45	V
Average Rectified Forward Current (Rated V_R , T_C = 105°C) Per Device Per Diode	I _{F(AV)}	30 15	Α
Peak Repetitive Forward Current, (Rated V _R , Square Wave, 20 kHz) Per Diode	I _{FRM}	30	Α
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	200	Α
Peak Repetitive Reverse Current (2.0 μs, 1.0 kHz) Per Diode (See Figure 6)	I _{RRM}	2.0	Α
Storage Temperature Range	T _{stg}	-65 to +175	°C
Operating Junction Temperature (Note 1)	T_J	-65 to +175	°C
Peak Surge Junction Temperature (Forward Current Applied)	T _{J(pk)}	175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs

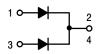
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

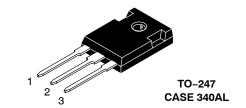


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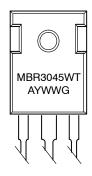
www.onsemi.com

SCHOTTKY BARRIER RECTIFIER 30 AMPERES, 45 VOLTS





MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MBR3045WTG	TO-247 (Pb-Free)	30 Units/Rail

The heat generated must be less than the thermal conductivity from Junction-to-Ambient: dP_D/dT_J < 1/R_{θJA}.
 *For additional information on our Pb-Free strategy and soldering details, please

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR3045WTG

THERMAL CHARACTERISTICS (Per Diode)

Rating		Max	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ heta JC} \ R_{ heta JA}$	1.4 40	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode)

Instantaneous Forward Voltage (Note 2)	٧F		V
$(i_F = 20 \text{ Amps}, T_C = 125^{\circ}C)$		0.62	
$(i_F = 30 \text{ Amps}, T_C = 125^{\circ}C)$		0.72	
$(i_F = 30 \text{ Amps}, T_C = 25^{\circ}C)$		0.76	
Instantaneous Reverse Current (Note 2)	i _R		mA
(Rated dc Voltage, T _C = 125°C)		100	
(Rated dc Voltage, T _C = 25°C)		1.0	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

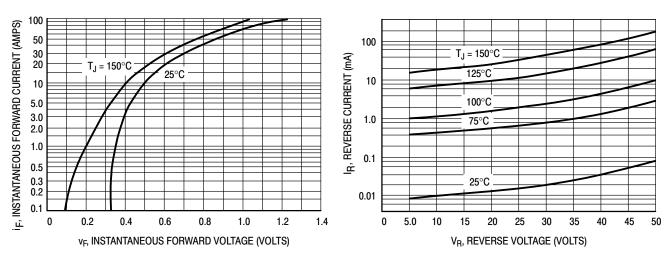


Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

MBR3045WTG

TYPICAL CHARACTERISTICS

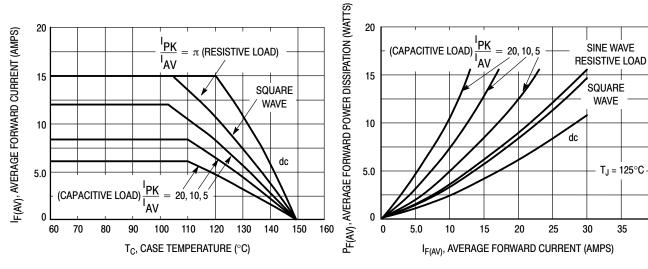


Figure 3. Current Derating (Per Leg)

Figure 4. Forward Power Dissipation (Per Leg)

40

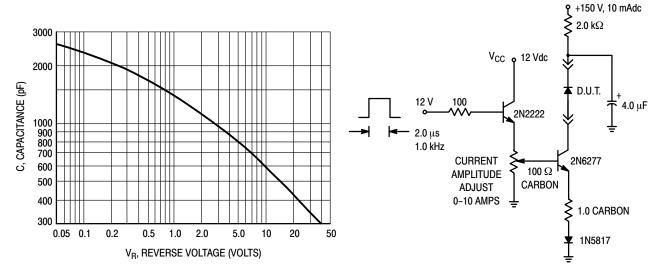
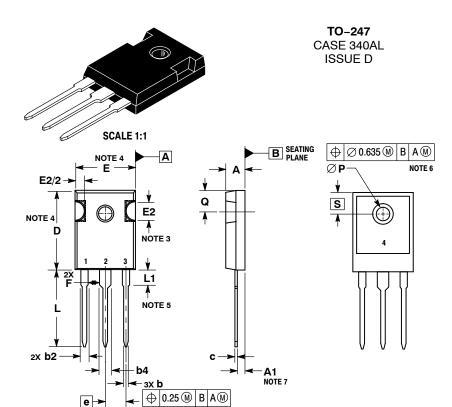


Figure 5. Capacitance

Figure 6. Test Circuit for Repetitive Reverse Current



DATE 17 MAR 2017

- NOTES:

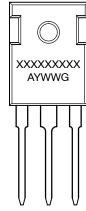
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.

 - DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH.
 MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY
 - LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY
- ©P SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.

 DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.70	5.30	
A1	2.20	2.60	
b	1.07	1.33	
b2	1.65	2.35	
b4	2.60	3.40	
С	0.45	0.68	
D	20.80	21.34	
E	15.50	16.25	
E2	4.32	5.49	
е	5.45 BSC		
F	2.655		
L	19.80	20.80	
L1	3.81	4.32	
P	3.55	3.65	
Q	5.40	6.20	
S	6.15 BSC		

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

Υ = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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